



**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(use as many sheets as necessary)

Complete if Known

Application Number	10/699,574
	October 31

Application Number	100-441100
Filing Date	October 31, 2003

Filing Date	
First Named Inventor	Ge, et al.

First Named Inventor	2011-2826
Art Unit	100-Munh

Art Unit	780- M 11
Examiner Name	TSM03-0660

Sheet 1 of 5

Sheet		1	of	5	Attorney Docket Number
U.S. PATENT DOCUMENTS					Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
Examiner Initials*	Cite No.	Document Number Number - Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	
MLT	1	US-4,072,974	02-07-1978	Ipri	
	2	US-4,631,803	12-30-1986	Hunter, et al.	
	3	US-5,013,681	05-07-1991	Godbey, et al.	
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	9	US-5,468,657	11-21-1995	Hsu	
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	35	US-6,410,371 B1	06-25-2002	Yu, et al.	
MLT	36	US-6,410,938 B1	06-25-2002	Xiang	

Minhloan Tran

Date _____

Considered

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Examiner Signature	Minhloan Tran	Date	7/20/00
<p>*EXAMINER: Initial if reference considered, whether or not citation is in conformance and not considered. Include copy of this form with next communication to applicant. *Applicant's unique citation designation number (optional). *See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. *Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). *For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. *Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. *Applicant is to place a check mark here if English language Translation is attached.</p>		Considered	
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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				Application Number	10/699,574
				Filing Date	October 31, 2003
				First Named Inventor	Ge, et al.
				Art Unit	2811 2826
				Examiner Name	TBD - Minh Loan Tran
				Attorney Docket Number	TSM03-0660
Sheet	2	of	5		

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Examiner Signature	Minh loan Tran	Date Considered	1/05
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				Application Number	10/699,574
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Filing Date	October 31, 2003
				First Named Inventor	Ge, et al.
				Art Unit	2844 2826
				Examiner Name	IBD Minhloan Tran
				Attorney Docket Number	TSM03-0660
Sheet	3	of	5		

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cita No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	2
MLT	47	ISMAIL, K., et al., "Electron Transport Properties of Si/SiGe Heterostructures: Measurements and Device Implications," Applied Physics Letter, Vol. 63, No. 5, (August 2, 1993), pp. 660-662.	
	48	NAYAK, D.K., et al., "Enhancement-Mode Quantum-Well Ge ₂ Si _{1-x} PMOS," IEEE Electron Device Letters, Vol. 12, No. 4, (April 1991), pp. 154-156.	
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	51	MIZUNO, T., et al., "Novel SOI p-Channel MOSFETs With Higher Strain in Si Channel Using Double SiGe Heterostructures," IEEE Transactions on Electron Devices, Vol. 49, No. 1, (January 2002), pp. 7-14.	
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	57	OOTSUKA, F., et al., "A Highly Dense, High-Performance 130nm Node CMOS Technology for Large Scale System-on-a-Chip Applications," International Electron Device Meeting, (2000), pp. 575-578.	
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Examiner Signature	Minhloan Tran	Date Considered	1/05
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				Art Unit	2844 2826
				Examiner Name	TBD- Minhloan Tran
Sheet	4	of	5	Attorney Docket Number	TSM03-0660

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS				
Examiner Initials*	Cita No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.		
MLT	60	MATTHEWS, J.W., et al., "Defects in Epitaxial Multilayers – III. Preparation of Almost Perfect Multilayers," Journal of Crystal Growth, Vol. 32, (1976), pp. 265-273.		
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	63	CURRENT, M.L., et al., "Atomic-Layer Cleaving and Non-Contact Thinning and Thickening for Fabrication of Laminated Electronic and Photonic Materials," 2001 Materials Research Society Spring Meeting (April 16-20, 2001).		
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